

Abstracts

A 1.9 GHz single-chip RF front-end GaAs MMIC with low-distortion cascode FET mixer for personal handy-phone system terminals (1998 [RFIC])

M. Nakayama, K. Horiguchi, K. Yamamoto, Y. Yoshii, S. Sugiyama, N. Suematsu and T. Takagi. "A 1.9 GHz single-chip RF front-end GaAs MMIC with low-distortion cascode FET mixer for personal handy-phone system terminals (1998 [RFIC])." 1998 Radio Frequency Integrated Circuits (RFIC) Symposium 98. (1998 [RFIC]): 205-208.

This paper describes new single-chip RF front-end GaAs MMIC for 1.9 GHz Japanese PHS handheld terminals. The IC consists of a high power amplifier, a T/R switch, a low noise amplifier, a newly developed low distortion cascode FET mixer and a negative voltage generator for FET gate bias voltage. The IC has high performance as RF front-end for terminals.

 [Return to main document.](#)